

# NB3F8L3010C

## 3.3V / 2.5V / 1.8V / 1.5V 3:1:10 LVCMOS Fanout Buffer

### Description

The NB3F8L3010C is a 3:1:10 Clock / Data fanout buffer operating on a 3.3 V / 2.5 V Core  $V_{DD}$  and two flexible 3.3 V / 2.5 V / 1.8 V / 1.5 V  $V_{DDO_n}$  supplies which must be equal or less than  $V_{DD}$ .

A Mux selects between a Crystal input, or either of two differential/SE Clock / Data inputs. Differential Inputs accept LVPECL, LVDS, HCSL, or SSTL and Single-Ended levels. The MUX control lines, SEL0 and SEL1, select  $CLK0/\overline{CLK0}$ ,  $CLK1/\overline{CLK1}$ , or Crystal input pins per Table 3. The Crystal input is disabled when a Clock input is selected. Output enable pin, OE, synchronously forces a High Impedance state (HZ) when Low per Table 4.

Outputs consist of 10 single-ended LVCMOS outputs.

### Features

- Ten CMOS / LVTTTL Outputs up to 200 MHz
- Differential Inputs Accept LVPECL, LVDS, HCSL, or SSTL
- Crystal Oscillator Interface
- Crystal Input Frequency Range: 10 MHz to 50 MHz
- Output Skew: 10 ps Typical
- Additive RMS Phase Jitter @ 125 MHz, (12 kHz – 20 MHz): 0.03 ps (Typical)
- Synchronous Output Enable
- Output Defined Level When Input is Floating
- Power Supply Modes:
  - ◆ Single 3.3 V
  - ◆ Single 2.5 V
  - ◆ Mixed 3.3 V  $\pm$  5% Core/2.5 V  $\pm$  5% Output Operating Supply
  - ◆ Mixed 3.3 V  $\pm$  5% Core/1.8 V  $\pm$  0.2 V Output Operating Supply
  - ◆ Mixed 3.3 V  $\pm$  5% Core/1.5 V  $\pm$  0.15 V Output Operating Supply
  - ◆ Mixed 2.5 V  $\pm$  5% Core/ 1.8 V  $\pm$  0.2 V Output Operating Supply
  - ◆ Mixed 2.5 V  $\pm$  5% Core /1.5 V  $\pm$  0.15 V Output Operating Supply
- Two Separate Output Bank Power Supplies
- Industrial temp. range -40°C to 85°C
- These are Pb-Free Devices

### Applications

- Clock Distribution
- Networking and Communications
- High End Computing
- Wireless and Wired Infrastructure

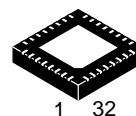
### End Products

- Servers
- Ethernet Switch/Routers
- ATE
- Test and Measurement



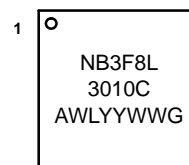
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QFN32  
G SUFFIX  
CASE 488AM

### MARKING DIAGRAM



A = Assembly Location  
WL = Wafer Lot  
YY = Year  
WW = Work Week  
G = Pb-Free Package

### ORDERING INFORMATION

See detailed ordering and shipping information page 12 of this data sheet.

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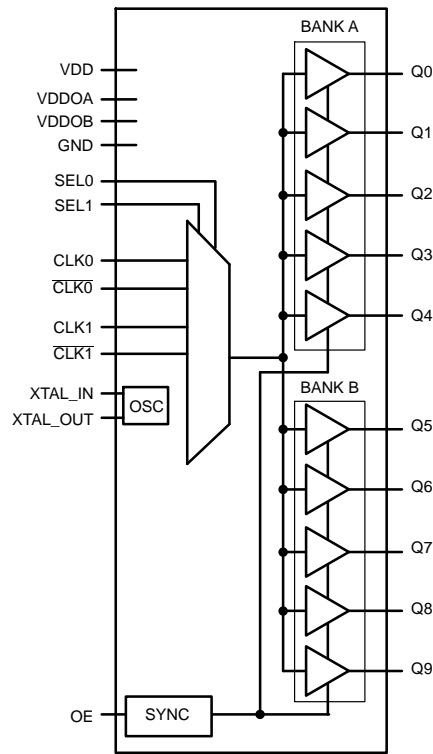


Figure 1. Simplified Logic Diagram

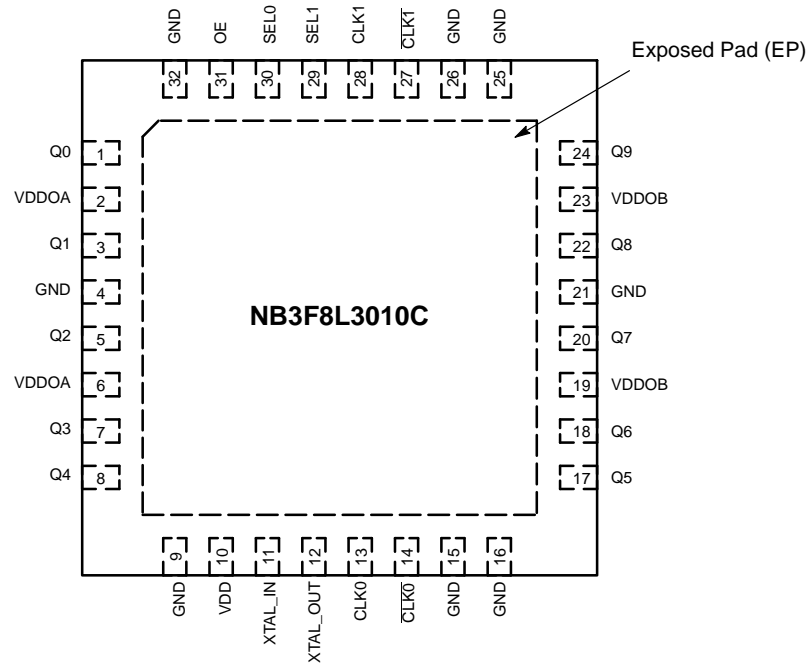


Figure 2. Pinout Configuration (Top View)

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**Table 1. PIN DESCRIPTION**

| Number                       | Name                     | Type                   | Input Default     | Description   |
|------------------------------|--------------------------|------------------------|-------------------|---|
| 1, 3, 5, 7, 8                | Q0, Q1, Q2, Q3, Q4       | LVC MOS                |                   | Outputs – Bank A  |
| 17, 18, 20, 22, 24           | Q5, Q6, Q7, Q8, Q9       | LVC MOS                |                   | Outputs – Bank B  |
| 2, 6                         | VDDOA                    | Power                  |                   | Positive Supply Pins for Bank A Outputs Q0 – Q4   |
| 19, 23                       | VDDOB                    | Power                  |                   | Positive Supply Pins for Bank B Outputs Q5 – Q9   |
| 4, 9, 15, 16, 21, 25, 26, 32 | GND                      | GND                    |                   | Ground Supply   |
| 10                           | VDD                      | Power                  |                   | V <sub>DD</sub> Positive Supply pin for Core and Inputs.  |
| 11                           | XTAL_IN                  | XTAL OSC / CLK Input   |                   | Crystal Oscillator Interface or External Clock Source at LVC MOS Levels   |
| 12                           | XTAL_OUT                 | XTAL OSC Output        |                   | Crystal Oscillator Interface  |
| 13                           | CLK0                     | Diff / SE Input        | Pulldown          | Non-inverting clock/data input 0.   |
| 14                           | $\overline{\text{CLK0}}$ | Diff / SE Input        | Pullup / Pulldown | Inverting differential clock input 0.   |
| 27                           | $\overline{\text{CLK1}}$ | Diff / SE Input        | Pullup / Pulldown | Inverting differential clock input 1  |
| 28                           | CLK1                     | Diff / SE Input        | Pulldown          | Non-inverting clock/data input 1  |
| 29                           | SEL1                     | LVC MOS / LV TTL Input | Pulldown          | Input clock select. See Table 3 for function. Input Pulldown  |
| 30                           | SEL0                     | LVC MOS / LV TTL Input | Pulldown          | Input clock select. See Table 3 for function. Input Pulldown  |
| 31                           | OE                       | LVC MOS / LV TTL Input | Pulldown          | Output Enable Control. See Table 4 for function.  |
| –                            | EP                       | –                      |                   | The Exposed Pad (EP) on the QFN–32 package bottom is thermally connected to the die for improved heat transfer out of package. The exposed pad must be attached to a heat-sinking conduit. The pad is electrically connected to the die, and must be electrically connected to GND. |

1. All VDD, VDDO<sub>n</sub> and GND pins must be externally connected to a power supply to guarantee proper operation. Bypass each V<sub>DD</sub> and VDDO<sub>n</sub> with 0.01  $\mu$ F CAP to GND.

**Table 2. PIN CHARACTERISTICS**

| Symbol           | Parameter  | Min | Typ | Max | Unit       |
|------------------|--|-----|-----|-----|------------|
| C <sub>IN</sub>  | Input Capacitance  |     | 4   |     | pF         |
| R                | Input Pulldown Resistor; Input Pulldown Resistor   |     | 50  |     | k $\Omega$ |
| C <sub>PD</sub>  | Power Dissipation Capacitance (per output)<br>VDDO = 3.3 V<br>VDDO = 2.5 V<br>VDDO = 1.8 V<br>VDDO = 1.5 V |     |     |     | pF         |
| R <sub>OUT</sub> | Output Impedance<br>VDDO = 3.3 V<br>VDDO = 2.5 V<br>VDDO = 1.8 V<br>VDDO = 1.5 V                           |     | 20  |     | $\Omega$   |

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## FUNCTION TABLES

**Table 3. CLOCK ENABLE (SELx) FUNCTION TABLE**

| SEL[1:0] Input | Selected Input Clock |
|----------------|----------------------|
| 00             | CLK0/CLK0            |
| 01             | CLK1/CLK1            |
| 10             | Crystal Osc Input    |
| 11             | Crystal Osc Input    |

**Table 5. DIFF IN/OUT TABLE (Diff or S.E.)**

| Input Condition             | Output     |
|-----------------------------|------------|
| CLK0/1; CLK0/1 = OPEN       | Logic LOW  |
| CLK0/1; CLK0/1 = GND        | Undefined  |
| CLK0/1 = HIGH; CLK0/1 = LOW | Logic HIGH |
| CLK0/1 = LOW; CLK0/1 = HIGH | Logic LOW  |

**Table 4. CLOCK OUTPUT ENABLE (OE) FUNCTION TABLE**

| OE Input | Q[9:0] Output   |
|----------|-----------------|
| 0        | High Impedance  |
| 1        | Outputs Enabled |

**Table 6. CRYSTAL CHARACTERISTICS**

| Parameter                          | Min         | Typ | Max | Unit     |
|------------------------------------|-------------|-----|-----|----------|
| Mode of Oscillation                | Fundamental |     |     |          |
| Frequency                          | 10          |     | 50  | MHz      |
| Equivalent Series Resistance (ESR) |             |     | 50  | $\Omega$ |
| Shunt Capacitance                  |             |     | 7   | pF       |
| Drive Power                        |             |     | 100 | $\mu$ W  |

**Table 7. ATTRIBUTES**

| Characteristic   | Value                |
|--|----------------------|
| ESD Protection<br>Human Body Model<br>Machine Model    | >2 kV<br>200 V       |
| Moisture Sensitivity (Note 2)<br>QFN32                 | Level 3              |
| Flammability Rating<br>Oxygen Index: 28 to 34          | UL 94 V-0 @ 0.125 in |
| Transistor Count                                       | 474 Devices          |
| Meets or exceeds JEDEC Spec EIA/JESD78 IC Latchup Test |                      |

2. For additional information, see Application Note AND8003/D.

**Table 8. MAXIMUM RATINGS** (Note 3)

| Symbol  | Parameter   | Condition          | Rating  | Unit |
|---|---|--------------------|---|------|
| V <sub>DD</sub> ,<br>V <sub>DDO<sub>n</sub></sub> | Positive Power Supply                             | GND = 0 V          | 4.6   | V    |
| V <sub>I</sub>                                    | Input Voltage<br>XTAL_IN<br>Diff, SELx, OE Inputs |                    | $0 \leq V_I \leq V_{DD}$<br>$-0.5 \leq V_I \leq V_{DD} + 0.5$ | V    |
| V <sub>O</sub>                                    | Output Voltage                                    |                    | $-0.5 \leq V_O \leq V_{DDO_n} + 0.5$                          | V    |
| T <sub>A</sub>                                    | Operating Temperature Range, Industrial           |                    | -40 to +85  | °C   |
| T <sub>stg</sub>                                  | Storage Temperature Range                         |                    | -65 to +150   | °C   |
| $\theta_{JA}$                                     | Thermal Resistance (Junction-to-Ambient)          | 0 lfpm<br>500 lfpm | 31<br>27  | °C/W |
| $\theta_{JC}$                                     | Thermal Resistance (Junction-to-Case)             | (Note 3)           | 12  | °C/W |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

3. JEDEC standard multilayer board – 2S2P (2 signal, 2 power).

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**Table 9. POWER SUPPLY DC CHARACTERISTICS**  $V_{DD} = 3.3\text{ V} \pm 5\%$  (3.135 V to 3.465 V) or  $V_{DD} = 2.5\text{ V} \pm 5\%$  (2.375 V to 2.625 V) and  $V_{DDO_n} = 3.3\text{ V} \pm 5\%$  (3.135 V to 3.465 V) or  $2.5\text{ V} \pm 5\%$  (2.375 V to 2.625 V) or  $1.8\text{ V} \pm 0.2\text{ V}$  (1.6 V to 2.0 V) or  $1.5\text{ V} \pm 0.15\text{ V}$  (1.35 V to 1.65 V);  $T_A = -40^\circ\text{C}$  to  $85^\circ\text{C}$

| Symbol | Parameter                 | Test Conditions   | Min | Typ | Max | Unit |
|--------|---------------------------|---|-----|-----|-----|------|
| IDD    | VDD Power Supply Current  | OE = 0, no load<br>$3.3\text{ V} \pm 5\%$ ; $V_{DDO_n} = 3.3\text{ V} \pm 5\%$ or $2.5\text{ V} \pm 5\%$ or $1.8\text{ V} \pm 0.2\text{ V}$ or $1.5\text{ V} \pm 0.15\text{ V}$<br>$2.5\text{ V} \pm 5\%$ ; $V_{DDO_n} = 2.5\text{ V} \pm 5\%$ or $1.8\text{ V} \pm 0.2\text{ V}$ or $1.5\text{ V} \pm 0.15\text{ V}$ |     | 30  | 50  | mA   |
| IDDO   | VDDO Power Supply Current | OE = 0, no load<br>$3.3\text{ V} \pm 5\%$ ; $V_{DDO_n} = 3.3\text{ V} \pm 5\%$ or $2.5\text{ V} \pm 5\%$ or $1.8\text{ V} \pm 0.2\text{ V}$ or $1.5\text{ V} \pm 0.15\text{ V}$<br>$2.5\text{ V} \pm 5\%$ ; $V_{DDO_n} = 2.5\text{ V} \pm 5\%$ or $1.8\text{ V} \pm 0.2\text{ V}$ or $1.5\text{ V} \pm 0.15\text{ V}$ |     |     | 5   | mA   |

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lpm.

**Table 10. DC CHARACTERISTICS**  $T_A = -40^\circ\text{C}$  to  $85^\circ\text{C}$

| Symbol      | Parameter   | Test Conditions   | Min                      | Typ | Max                              | Unit          |
|-------------|---|---|--------------------------|-----|----------------------------------|---------------|
| $V_{IH}$    | LVC MOS / LV TTL Input High Voltage (OE, SELx)  | $V_{DD} = 3.3\text{ V} \pm 5\%$<br>$V_{DD} = 2.5\text{ V} \pm 5\%$  | 2<br>1.7                 |     | $V_{DD} + 0.3$<br>$V_{DD} + 0.3$ | V             |
| $V_{IL}$    | LVC MOS / LV TTL Input Low Voltage (OE, SELx)   | $V_{DD} = 3.3\text{ V} \pm 5\%$<br>$V_{DD} = 2.5\text{ V} \pm 5\%$  | -0.3<br>-0.3             |     | 0.8<br>0.7                       | V             |
| $I_{IH}$    | Input High Current<br>OE, SELx,<br>CLKx/CLKx  | $V_{DD} = V_{IN} = 3.465\text{ V}$<br>$V_{DD} = V_{IN} = 3.465\text{ V}$ or $2.625\text{ V}$  |                          |     | 150<br>150                       | $\mu\text{A}$ |
| $I_{IL}$    | Input Low Current<br>OE, SELx<br>CLKx<br>CLKx   | $V_{DD} = 3.465\text{ V}$ ; $V_{IN} = 0.0\text{ V}$<br>$V_{DD} = 3.465\text{ V}$ or $2.625\text{ V}$ ; $V_{IN} = 0.0\text{ V}$<br>$V_{DD} = 3.465\text{ V}$ or $2.625\text{ V}$ ; $V_{IN} = 0.0\text{ V}$ | -5<br>-5<br>-150         |     |                                  | $\mu\text{A}$ |
| $V_{OH}$    | Output High Voltage (Note 4)  | $V_{DDO_n} = 3.3\text{ V} \pm 5\%$<br>$V_{DDO_n} = 2.5\text{ V} \pm 5\%$<br>$V_{DDO_n} = 1.8\text{ V} \pm 0.2\text{ V}$<br>$V_{DDO_n} = 1.5\text{ V} \pm 0.15\text{ V}$                                   | 2.6<br>1.8<br>1.2<br>0.9 |     |                                  | V             |
| $V_{OL}$    | Output Low Voltage (Note 4)   | $V_{DDO_n} = 3.3\text{ V} \pm 5\%$ or $2.5\text{ V} \pm 5\%$<br>$V_{DDO_n} = 1.8\text{ V} \pm 0.2\text{ V}$<br>$V_{DDO_n} = 1.5\text{ V} \pm 0.15\text{ V}$   |                          |     | 0.5<br>0.4<br>0.37               | V             |
| $V_{PP}$    | Peak-to-Peak Input Voltage<br>$V_{IL} > -0.3\text{ V}$<br>CLKx/CLKx                             | $V_{DD} = 3.3\text{ V} \pm 5\%$ or $V_{DD} = 2.5\text{ V} \pm 5\%$  | 0.15                     |     | 1.3                              | V             |
| $V_{IHCMR}$ | Input High Level Common Mode Range<br>$V_{CM} = V_{IH}$ ; $V_{IL} > -0.3\text{ V}$<br>CLKx/CLKx | $V_{DD} = 3.3\text{ V} \pm 5\%$ or $V_{DD} = 2.5\text{ V} \pm 5\%$  | 0.5                      |     | $V_{DD} - 0.85$                  | V             |

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lpm.

4. Outputs terminated with  $50\ \Omega$  to  $V_{DDO_n}/2$ . See Parameter Measurement Information..

**Table 11. AC CHARACTERISTICS**  $V_{DD} = 3.3\text{ V} \pm 5\%$  (3.135 V to 3.465 V) or  $V_{DD} = 2.5\text{ V} \pm 5\%$  (2.375 V to 2.625 V) and  $V_{DDO_n} = 3.3\text{ V} \pm 5\%$  (3.135 V to 3.465 V) or  $2.5\text{ V} \pm 5\%$  (2.375 V to 2.625 V) or  $1.8\text{ V} \pm 0.2\text{ V}$  (1.6 V to 2.0 V) or  $1.5\text{ V} \pm 0.15\text{ V}$  (1.35 V to 1.65 V);  $T_A = -40^\circ\text{C}$  to  $85^\circ\text{C}$

| Symbol    | Parameter        | Test Conditions                      | Min | Typ | Max | Unit |
|-----------|------------------|--------------------------------------|-----|-----|-----|------|
| $f_{MAX}$ | Output Frequency | Using External Crystal               | 10  |     | 50  | MHz  |
|           |                  | Using External Clock Source (Note 5) | DC  |     | 200 | MHz  |

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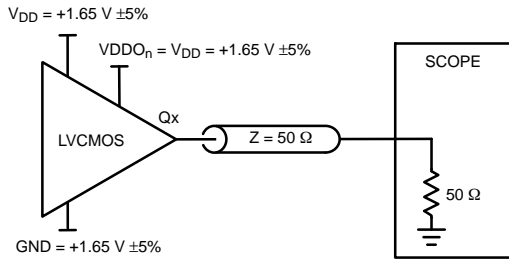
**Table 11. AC CHARACTERISTICS**  $V_{DD} = 3.3\text{ V} \pm 5\%$  (3.135 V to 3.465 V) or  $V_{DD} = 2.5\text{ V} \pm 5\%$  (2.375 V to 2.625 V) and  $V_{DDO_n} = 3.3\text{ V} \pm 5\%$  (3.135 V to 3.465 V) or  $2.5\text{ V} \pm 5\%$  (2.375 V to 2.625 V) or  $1.8\text{ V} \pm 0.2\text{ V}$  (1.6 V to 2.0 V) or  $1.5\text{ V} \pm 0.15\text{ V}$  (1.35 V to 1.65 V);  $T_A = -40^\circ\text{C}$  to  $85^\circ\text{C}$

| Symbol           | Parameter   |  | Test Conditions                              | Min | Typ  | Max | Unit   |
|------------------|---|--|--|-----|------|-----|--------|
| $t_{sk(o)}$      | Output Skew (Notes 6 and 7)                                     |  |  |     | 10   | 55  | ps     |
| $t_{JITTER\Phi}$ | Additive RMS Phase Jitter (Integrated 12 kHz – 20 MHz) (Note 8) | Input clock from CLK0/CLK0 or CLK1/CLK1      | $V_{DDO_n} = 3.3\text{ V} \pm 5\%$           |     | 0.03 |     | ps     |
|                  |   |  | $V_{DDO_n} = 2.5\text{ V} \pm 5\%$           |     | 0.03 |     |        |
|                  |   |  | $V_{DDO_n} = 1.8\text{ V} \pm 0.2\text{ V}$  |     | 0.03 |     |        |
|                  |   |  | $V_{DDO_n} = 1.5\text{ V} \pm 0.15\text{ V}$ |     | 0.03 |     |        |
|                  |   | External clock over drives crystal interface | $V_{DDO_n} = 3.3\text{ V} \pm 5\%$           |     | 0.03 |     |        |
|                  |   |  | $V_{DDO_n} = 2.5\text{ V} \pm 5\%$           |     | 0.03 |     |        |
|                  |   |  | $V_{DDO_n} = 1.8\text{ V} \pm 0.2\text{ V}$  |     | 0.03 |     |        |
|                  |   |  | $V_{DDO_n} = 1.5\text{ V} \pm 0.15\text{ V}$ |     | 0.03 |     |        |
|                  |   | Input clock from crystal                     | $V_{DDO_n} = 3.3\text{ V} \pm 5\%$           |     | 0.03 |     |        |
|                  |   |  | $V_{DDO_n} = 2.5\text{ V} \pm 5\%$           |     | 0.03 |     |        |
|                  |   |  | $V_{DDO_n} = 1.8\text{ V} \pm 0.2\text{ V}$  |     | 0.03 |     |        |
|                  |   |  | $V_{DDO_n} = 1.5\text{ V} \pm 0.15\text{ V}$ |     | 0.03 |     |        |
| $t_R / t_F$      | Output Rise/Fall Time (20% and 80%)                             |  | $V_{DDO_n} = 3.3\text{ V} \pm 5\%$           | 150 | 350  | 500 | ps     |
|                  |   |  | $V_{DDO_n} = 2.5\text{ V} \pm 5\%$           | 150 | 350  | 500 |        |
|                  |   |  | $V_{DDO_n} = 1.8\text{ V} \pm 0.2\text{ V}$  | 150 | 350  | 600 |        |
|                  |   |  | $V_{DDO_n} = 1.5\text{ V} \pm 0.15\text{ V}$ | 150 | 350  | 600 |        |
| odc              | Output Duty Cycle   |  | $V_{DDO_n} = 3.3\text{ V} \pm 5\%$           | 45  |      | 55  | %      |
|                  |   |  | $V_{DDO_n} = 2.5\text{ V} \pm 5\%$           | 40  |      | 60  |        |
|                  |   |  | $V_{DDO_n} = 1.8\text{ V} \pm 0.2\text{ V}$  | 40  |      | 60  |        |
|                  |   |  | $V_{DDO_n} = 1.5\text{ V} \pm 0.15\text{ V}$ | 40  |      | 60  |        |
| $t_{EN}$         | Output Enable Time (Note 9)                                     | OE   |  |     |      | 4   | cycles |
| $t_{DIS}$        | Output Disable Time (Note 9)                                    | OE   |  |     |      | 4   | cycles |
| MUX_ISOLATION    | MUX_ISOLATION   |  | 155.52 MHz                                   | 55  |      |     | dB     |

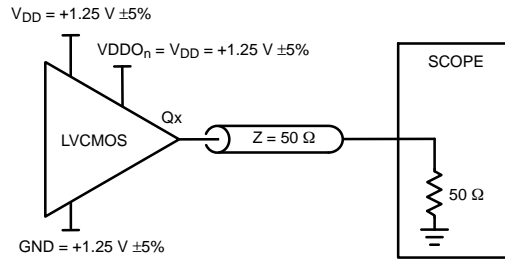
NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfm.

5. XTAL\_IN can be overdriven relative to a signal a crystal would provide.
6. Defined as skew between outputs at the same supply voltage and with equal load conditions. Measured at  $V_{DDO_n}/2$ .
7. This parameter is defined in accordance with JEDEC Standard 65.
8. See phase noise plot.
9. These parameters are guaranteed by characterization. Not tested in production. See Parameter Measurement Information

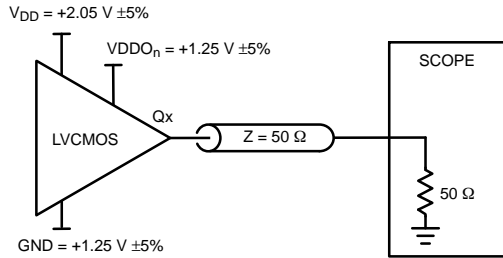
PARAMETER MEASUREMENT INFORMATION



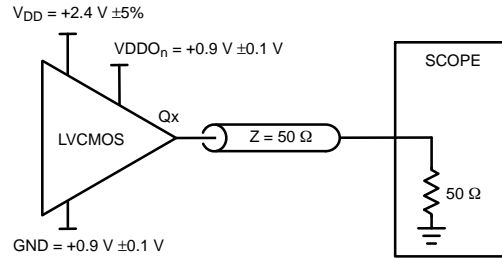
3.3 V Core / 3.3 V Output Load AC Test Circuit  
(Terminating to  $VDDO_n/2$ )



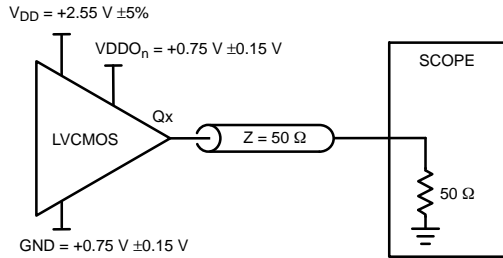
2.5 V Core / 2.5 V Output Load AC Test Circuit  
(Terminating to  $VDDO_n/2$ )



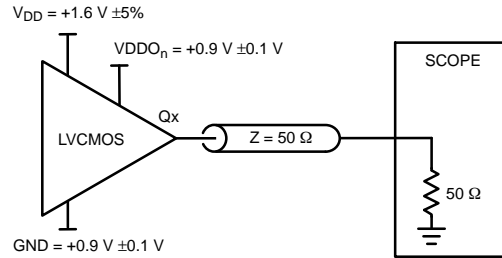
3.3 V Core / 2.5 V Output Load AC Test Circuit  
(Terminating to  $VDDO_n/2$ )



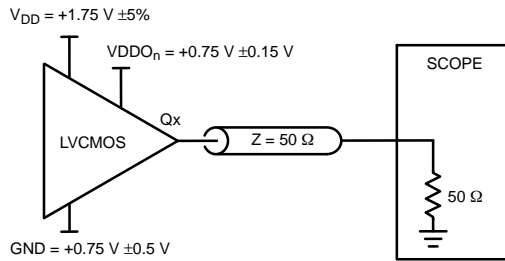
3.3 V Core / 1.8 V Output Load AC Test Circuit  
(Terminating to  $VDDO_n/2$ )



3.3 V Core / 1.5 V Output Load AC Test Circuit  
(Terminating to  $VDDO_n/2$ )



2.5 V Core / 1.8 V Output Load AC Test Circuit  
(Terminating to  $VDDO_n/2$ )



2.5 V Core / 1.5 V Output Load AC Test Circuit  
(Terminating to  $VDDO_n/2$ )

Figure 3. Operational Supply and Termination Test Conditions

PARAMETER MEASUREMENT INFORMATION

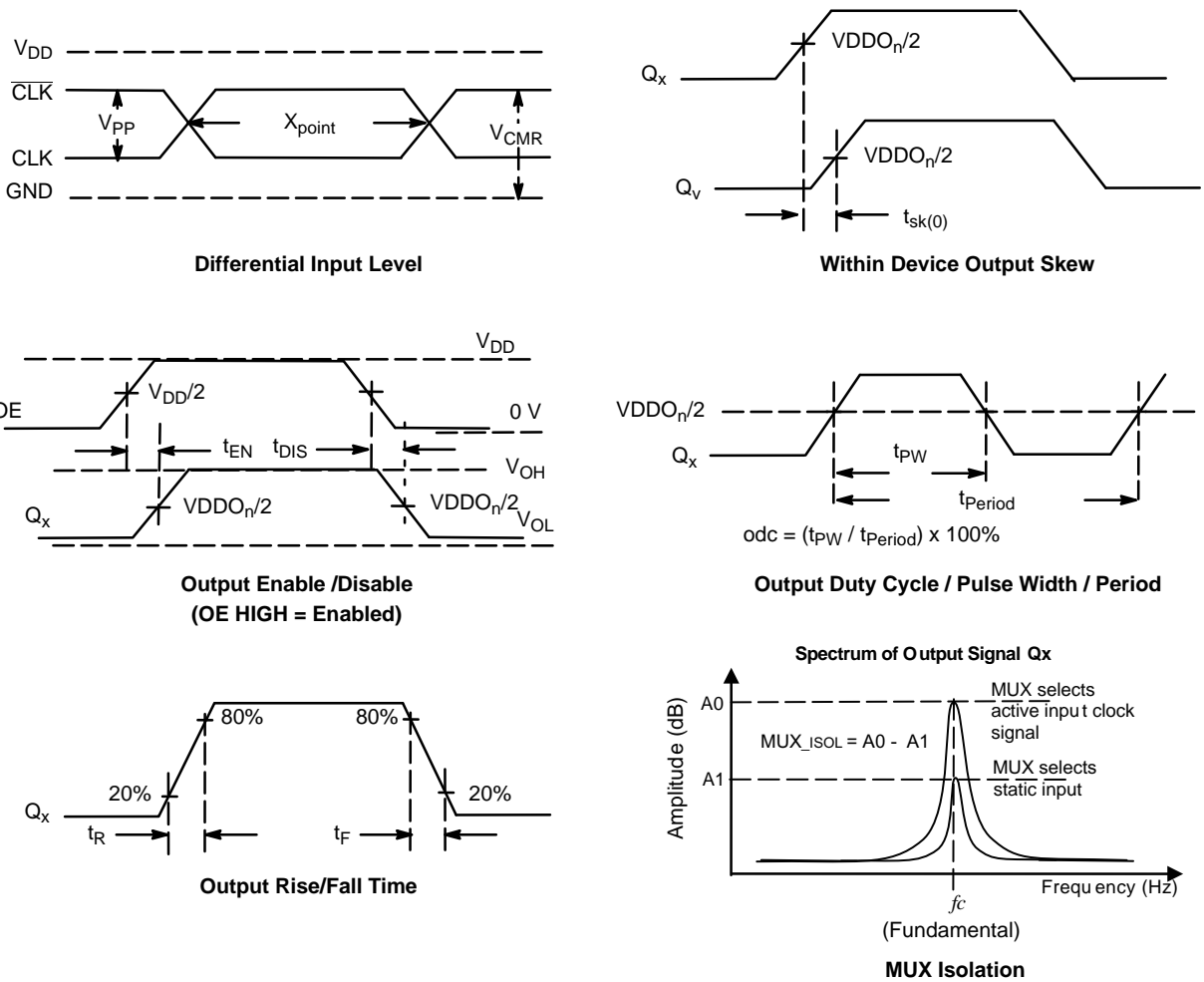


Figure 4. Operational Waveforms and MUX Input Isolation Plot

APPLICATION INFORMATION

Recommendations for Unused LVC MOS Output Pins

Inputs:

CLK/CLK Inputs

For applications not requiring the use of the differential input, both CLK and  $\overline{\text{CLK}}$  can be left floating. Though not required, but for additional protection, a 1 k $\Omega$  resistor can be tied from CLK to ground.

Crystal Inputs

For applications not requiring the use of the crystal oscillator input, both XTAL\_IN and XTAL\_OUT can be left floating. Though not required, but for additional protection, a 1 k $\Omega$  resistor can be tied from XTAL\_IN to ground.

LVC MOS Outputs

A 33  $\Omega$  series terminating resistor may be used on each clock output if the trace is longer than 1 inch.

LVC MOS Control Pins

All control pins have internal pulldowns; additional resistance is not required but can be added for additional protection. A 1 k $\Omega$  resistor can be used.

Power Supplies

VDD is the power supply for the core and input circuitry.

VDDOA and VDDOB are two separate positive power supplies for two banks of outputs:

VDDOA pins 2 and 6 are connected internally for outputs Q0 – Q4.

VDDOB pins 19 and 23 are connected internally for outputs Q5 – Q9.



### Differential Input with Single-Ended Interconnect

Refer to Figure 5 to interconnect a single-ended to a Differential Pair of inputs. The reference bias voltage  $V_{REF} = V_{DD}/2$  is generated by the resistor divider of R3 and R4. Bypass capacitor (C1) can filter noise on the DC bias. This bias circuit should be located as close to the input pin as possible. Adjust R1 and R2 to common mode voltage of the signal input swing to preserve duty cycle.

This configuration requires that the sum of the output impedance of the driver ( $R_o$ ) and the series resistance ( $R_s$ ) equals the transmission line impedance. In addition, matched termination by R1 and R2 will attenuate the signal

amplitude in half. Termination may be done by using  $R_s$  or by using R1 and R2. First,  $R_s = 0$  and then R3 and R4 in parallel should equal the transmission line impedance. For most 50  $\Omega$  applications, R1 and R2 can be 100  $\Omega$ . The differential input can handle full rail LVCMOS signaling, but it is recommended that the amplitude be reduced. The datasheet specifies a differential amplitude which needs to be doubled for a single ended equivalent stimulus.  $V_{ILmin}$  cannot be less than  $-0.3$  V and  $V_{IHmax}$  cannot be more than  $V_{DD} + 0.3$  V. The datasheet specifications are characterized and guaranteed by using a differential signal.

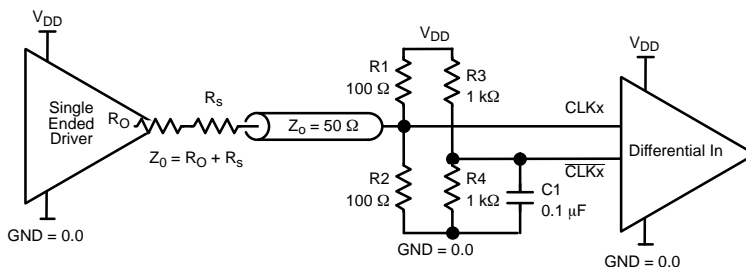


Figure 5. Differential Input with Single-ended Interconnect

### Crystal Input Interface

The device has been characterized with 18 pF parallel resonant crystals. The capacitor values, C1 and C2, shown in Figure 6 below as 15 pF were determined using an 18 pF parallel resonant crystal and were chosen to minimize the ppm error. The optimum C1 and C2 values can be slightly adjusted for different board layouts.

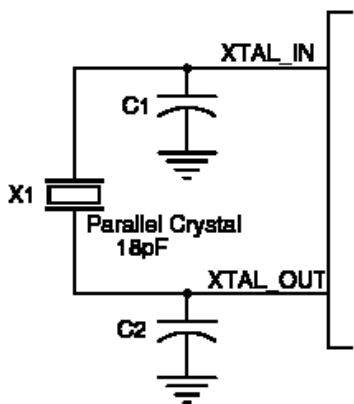


Figure 6. Crystal Input Interface

### CLOCK Overdriving the XTAL Interface

The XTAL\_IN input can accept a single-ended LVCMOS signal through an AC coupling capacitor. A general LVCMOS interface diagram is shown in Figure 7 and a general LVPECL interface in Figure 8. The XTAL\_OUT pin must be left floating. The maximum amplitude of the input signal should not exceed 2 V and the input edge rate can be as slow as 10 ns. This configuration requires that the output impedance of the driver ( $R_o$ ) plus the series resistance ( $R_s$ ) equals the transmission line impedance. In addition, matched termination at the crystal input will attenuate the signal in half. This can be done in one of two ways. First, R1 and R2 in parallel should equal the transmission line impedance. For most 50  $\Omega$  applications, R1 and R2 can be 100  $\Omega$ . This can also be accomplished by removing R1 and making R2 50  $\Omega$ . By overdriving the crystal oscillator, the device will be functional, but note, the device performance is guaranteed by using a quartz crystal.

# NB3F8L3010C

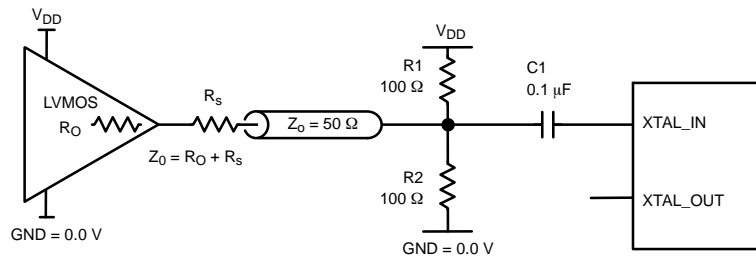


Figure 7. General Diagram for LVMOS Driver to XTAL Input Interface Use  $R_S$  or  $R1 / R2$

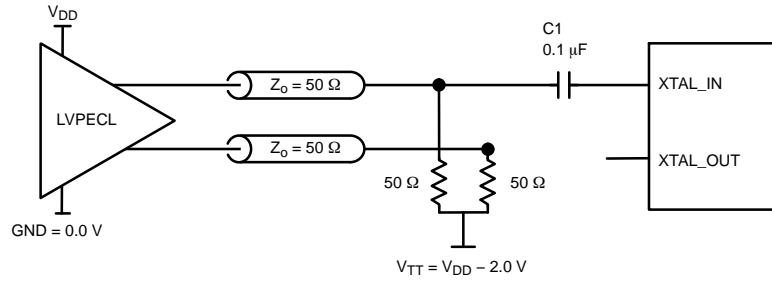
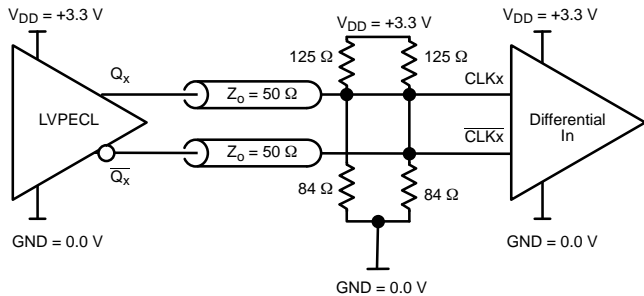


Figure 8. General Diagram for LVPECL Driver to XTAL Input Interface

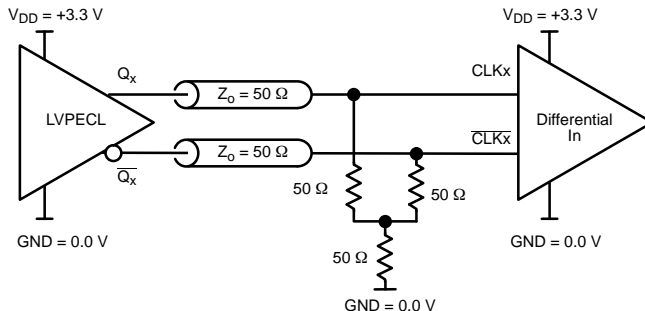
**Differential Clock Input Interface**

The CLK /  $\overline{\text{CLK}}$  accept LVDS, LVPECL, SSTL, HCSL differential signals. Signals must meet the  $V_{PP}$  and  $V_{CMR}$  input requirements. Figures 9 to 13 show interface examples for the CLK /  $\overline{\text{CLK}}$  input with built-in 50  $\Omega$  terminations driven by the most common driver types. The

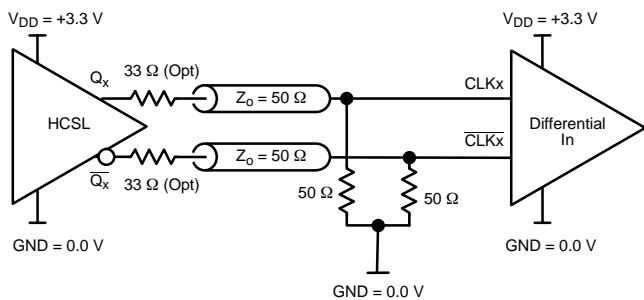
input interfaces suggested here are examples only. If the driver is from another vendor, use their termination recommendation. Please consult with the vendor of the driver component to confirm the driver termination requirements.



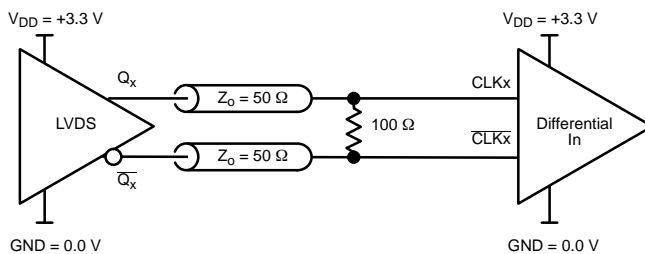
**Figure 9. CLK /  $\overline{\text{CLK}}$  Input Driven by 3.3 V LVPECL Driver (Thevenin Parallel Termination)**



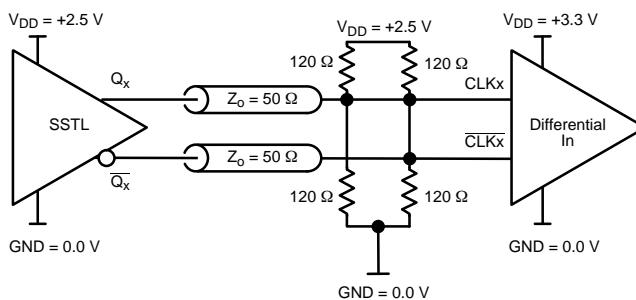
**Figure 10. CLK /  $\overline{\text{CLK}}$  Input Driven by 3.3 V LVPECL Driver ("Y" Parallel Termination)**



**Figure 11. CLK /  $\overline{\text{CLK}}$  Input Driven by a 3.3 V HCSL Driver**



**Figure 12. CLK /  $\overline{\text{CLK}}$  Input Driven by 3.3 V LVDS Driver**



**Figure 13. CLK /  $\overline{\text{CLK}}$  Input Driven by 2.5 V SSTL Driver**

## NB3F8L3010C

### VFQFN EPAD Thermal Release Path

In order to maximize both the removal of heat from the package and the electrical performance, a land pattern must be incorporated on the Printed Circuit Board (PCB) within the footprint of the package corresponding to the exposed metal pad or exposed heat slug on the package, as shown in Figure 14. The solderable area on the PCB, as defined by the solder mask, should be at least the same size/shape as the exposed pad/slug area on the package to maximize the thermal/electrical performance. Sufficient clearance should be designed on the PCB between the outer edges of the land pattern and the inner edges of pad pattern for the leads to avoid any shorts. While the land pattern on the PCB provides a means of heat transfer and electrical grounding from the package to the board through a solder joint, thermal vias are necessary to effectively conduct from the surface of the PCB to the ground plane(s). The land pattern must be connected

to ground through these vias. The vias act as “heat pipes”. The number of vias (i.e. “heat pipes”) is application specific and dependent upon the package power dissipation as well as electrical conductivity requirements. Thus, thermal and electrical analysis and/or testing are recommended to determine the minimum number needed. Maximum thermal and electrical performance is achieved when an array of vias is incorporated in the land pattern. It is recommended to use as many vias connected to ground as possible. It is also recommended that the via diameter should be 12 to 13 mils (0.30 to 0.33 mm) with 1 oz copper via barrel plating. This is desirable to avoid any solder wicking inside the via during the soldering process which may result in voids in solder between the exposed pad/slug and the thermal land. Precautions should be taken to eliminate any solder voids between the exposed heat slug and the land pattern. Note: These recommendations are to be used as a guideline only.

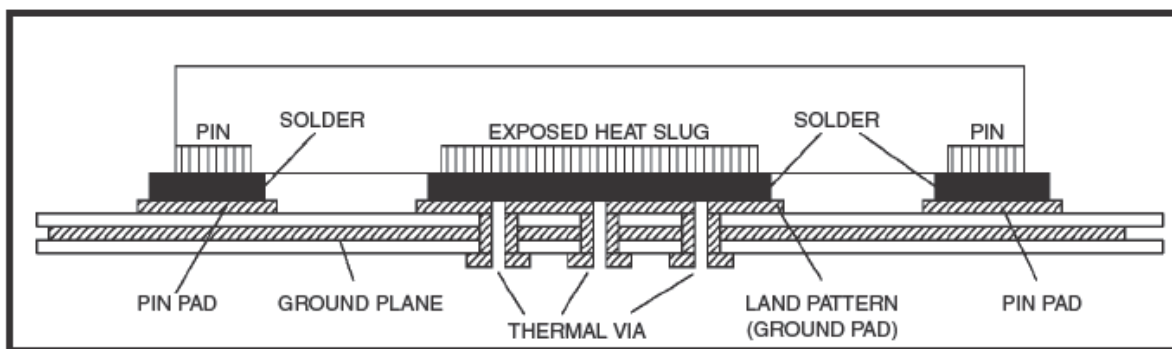


Figure 14. Suggested Assembly for Exposed Pad Thermal Release Path – Cut-away View (not to scale)

### ORDERING INFORMATION

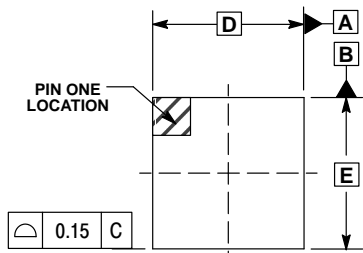
| Device           | Package            | Shipping†          |
|------------------|--------------------|--------------------|
| NB3F8L3010CMNG   | QFN32<br>(Pb-Free) | 74 Units / Rail    |
| NB3F8L3010CMNR4G | QFN32<br>(Pb-Free) | 1000 / Tape & Reel |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

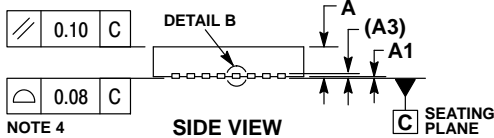
# NB3F8L3010C

## PACKAGE DIMENSIONS

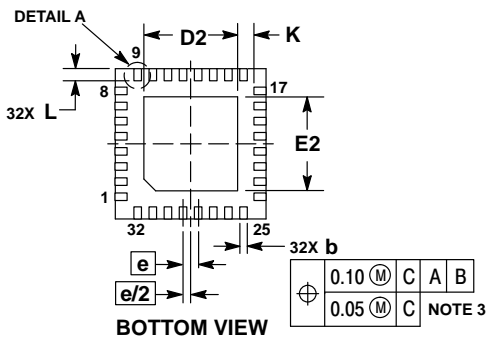
QFN32 5x5, 0.5P  
CASE 488AM  
ISSUE A



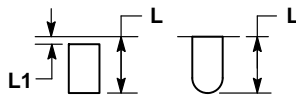
TOP VIEW



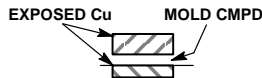
SIDE VIEW



BOTTOM VIEW



DETAIL A  
ALTERNATE TERMINAL  
CONSTRUCTIONS



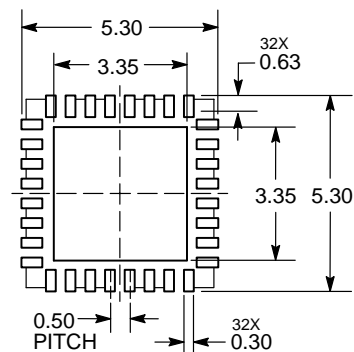
DETAIL B  
ALTERNATE  
CONSTRUCTION

NOTES:

1. DIMENSIONS AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.30MM FROM THE TERMINAL TIP.
4. COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.

| MILLIMETERS |      |      |
|-------------|------|------|
| DIM         | MIN  | MAX  |
| A           | 0.80 | 1.00 |
| A1          | ---  | 0.05 |
| A3          | 0.20 | REF  |
| b           | 0.18 | 0.30 |
| D           | 5.00 | BSC  |
| D2          | 2.95 | 3.25 |
| E           | 5.00 | BSC  |
| E2          | 2.95 | 3.25 |
| e           | 0.50 | BSC  |
| K           | 0.20 | ---  |
| L           | 0.30 | 0.50 |
| L1          | ---  | 0.15 |

### RECOMMENDED SOLDERING FOOTPRINT\*



DIMENSION: MILLIMETERS

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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